| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 29 | 27002 | ((chemical near5 mechanical near5 polish$3) CMP) | USPAT; US-PGPUB | 2003/05/28 19:05 |
| 30 | 12626 | (((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon)) | USPAT; US-PGPUB | 2003/05/28 19:06 |
| 31 | 8056 | ((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6 | USPAT; US-PGPUB | 2003/05/28 19:06 |
| 36 | 4447 | (((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate | USPAT; US-PGPUB | 2003/05/28 18:36 |
| 37 | 3681 | ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (first near5 (layer material film)) | USPAT; US-PGPUB | 2003/05/28 18:37 |
| 38 | 3488 | ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (second near5 (layer material film)) | USPAT; US-PGPUB | 2003/05/28 18:38 |
| 39 | 1588 | ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (third near5 (layer material film)) | USPAT; US-PGPUB | 2003/05/28 18:39 |
| 40 | 3298 | (((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (first near5 (layer material film))) and ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (second near5 (layer material film))) | USPAT; US-PGPUB | 2003/05/28 18:40 |
| 41 | 1526 | ((((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (first near5 (layer material film))) and ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (second near5 (layer material film))) and ((((((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon))) and selectiv$6) and rate) and (third near5 (layer material film))) | USPAT; US-PGPUB | 2003/05/28 18:41 |
| 42 | 9426 | ((chemical near5 mechanical near5 polish$3) CMP) | EPO; JPO; DERWENT; IBM_TDB | 2003/05/28 19:06 |
| 43 | 409 | (((chemical near5 mechanical near5 polish$3) CMP)) and ((insulat$3 dielectric oxide) and planar$6 and (conduct$6 polysilicon)) | EPO; JPO; DERWENT; IBM_TDB | 2003/05/28 19:06 |